



## 2N5770



### **NPN RF Transistor**

This device is designed for use as RF amplifiers, oscillators and multipliers with collector currents in the 1.0 mA to 30 mA range. Sourced from Process 43. See PN918 for characteristics.

### **Absolute Maximum Ratings\***

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CEO}$	Collector-Emitter Voltage	15	V
V <sub>CBO</sub>	Collector-Base Voltage	30	V
$V_{EBO}$	Emitter-Base Voltage	4.5	V
Ic	Collector Current - Continuous	50	mA
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

<sup>\*</sup>These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

### **Thermal Characteristics**

TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		2N5770	
P <sub>D</sub>	Total Device Dissipation Derate above 25°C	350 2.8	mW mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	125	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	°C/W

## **NPN RF Transistor**

(continued)

Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHA	RACTERISTICS				
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage*	$I_C = 3.0 \text{ mA}, I_B = 0$	15		V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	$I_C = 1.0 \mu\text{A}, I_E = 0$	30		V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	$I_E = 10  \mu A, I_C = 0$	4.5		V
CBO	Collector Cutoff Current	$V_{CB} = 15 \text{ V}, I_{E} = 0$		10	nA
		$V_{CB} = 15 \text{ V}, I_E = 0, T_A = 150 ^{\circ}\text{C}$		1.0	μΑ
EBO	Emitter Cutoff Current	$V_{EB} = 3.0 \text{ V}, I_{C} = 0$ $V_{EB} = 2.0 \text{ V}, I_{C} = 0$		10 1.0	μA 
		V <sub>EB</sub> = 2.0 V, I <sub>C</sub> = 0		1.0	μΑ
ON CHAF	RACTERISTICS*				
) <sub>FE</sub>	DC Current Gain	$V_{CE} = 1.0 \text{ V}, I_{C} = 3.0 \text{ mA}$	20 50	200	
/ <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	$V_{CE} = 10 \text{ V}, I_{C} = 8.0 \text{ mA}$ $I_{C} = 10 \text{ mA}, I_{B} = 1.0 \text{ mA}$	30	0.4	V
/ <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 10 mA, I <sub>B</sub> = 1.0 mA		1.0	V
	ONLAL CLUB A OTERIOTICS				
	GNAL CHARACTERISTICS			ı	
	GNAL CHARACTERISTICS  Noise Figure	$I_C = 1.0 \text{ mA}, V_{CE} = 8.0 \text{ V},$ $f = 60 \text{ MHz}, P_C = 400 \text{ O}$		6.0	dB
NF		$f = 60 \text{ MHz}, Rg = 400 \Omega$	0.7	6.0	dB pF
NF C <sub>cb</sub>	Noise Figure	$f = 60 \text{ MHz}, Rg = 400 \Omega$ $V_{CB} = 10 \text{ V}, I_{E} = 0, f = 1.0 \text{ MHz}$	0.7		
NF C <sub>cb</sub>	Noise Figure  Collector-Base Capacitance	$f = 60 \text{ MHz}, Rg = 400 \Omega$	0.7	1.1	pF
NF Ccb Cib	Noise Figure  Collector-Base Capacitance  Input Capacitance	$\begin{split} f &= 60 \text{ MHz}, \text{ Rg} = 400 \ \Omega \\ V_{CB} &= 10 \text{ V}, \text{ I}_{E} = 0, \text{ f} = 1.0 \text{ MHz} \\ V_{EB} &= 0.5 \text{ V} \\ I_{C} &= 8.0 \text{ mA}, \text{ V}_{CE} = 10 \text{ V}, \\ f &= 100 \text{ MHz} \end{split}$	9.0	1.1	pF
NF Ccb	Noise Figure  Collector-Base Capacitance  Input Capacitance	$\begin{split} &f=60 \text{ MHz},  Rg=400  \Omega \\ &V_{CB}=10  V,  I_E=0,  f=1.0  \text{MHz} \\ &V_{EB}=0.5  V \\ &I_C=8.0  \text{mA},  V_{CE}=10  V, \\ &f=100  \text{MHz} \\ &I_C=8.0  \text{mA},  V_{CE}=10  V, \end{split}$	9.0	1.1 2.0 18	pF
NF Docts Dib Mre	Noise Figure  Collector-Base Capacitance  Input Capacitance	$\begin{split} f &= 60 \text{ MHz}, \text{ Rg} = 400 \ \Omega \\ V_{CB} &= 10 \text{ V}, \text{ I}_{E} = 0, \text{ f} = 1.0 \text{ MHz} \\ V_{EB} &= 0.5 \text{ V} \\ I_{C} &= 8.0 \text{ mA}, \text{ V}_{CE} = 10 \text{ V}, \\ f &= 100 \text{ MHz} \end{split}$		1.1	pF
NF C <sub>cb</sub> Cib	Noise Figure  Collector-Base Capacitance  Input Capacitance  Small-Signal Current Gain	$\begin{split} &f=60 \text{ MHz},  Rg=400   \Omega \\ &V_{CB}=10  V,  I_E=0,  f=1.0   \text{MHz} \\ &V_{EB}=0.5   V \\ &I_C=8.0  \text{mA},  V_{CE}=10   V, \\ &f=100   \text{MHz} \\ &I_C=8.0   \text{mA},  V_{CE}=10   V, \\ &f=1.0   \text{kHz} \end{split}$	9.0	1.1 2.0 18 240	pF pF
SMALL SI	Noise Figure  Collector-Base Capacitance  Input Capacitance  Small-Signal Current Gain	$\begin{split} &f=60 \text{ MHz},  Rg=400  \Omega \\ &V_{CB}=10  V,  I_E=0,  f=1.0  \text{MHz} \\ &V_{EB}=0.5  V \\ &I_C=8.0  \text{mA},  V_{CE}=10  V, \\ &f=100  \text{MHz} \\ &I_C=8.0  \text{mA},  V_{CE}=10  V, \\ &f=1.0  \text{kHz} \\ &I_E=8.0  \text{mA},  V_{CB}=10  V, \end{split}$	9.0	1.1 2.0 18 240	pF pF
NF Ccb Cib lite b'Cc	Noise Figure  Collector-Base Capacitance  Input Capacitance  Small-Signal Current Gain	$\begin{split} &f=60 \text{ MHz},  Rg=400  \Omega \\ &V_{CB}=10  V,  I_E=0,  f=1.0  \text{MHz} \\ &V_{EB}=0.5  V \\ &I_C=8.0  \text{mA},  V_{CE}=10  V, \\ &f=100  \text{MHz} \\ &I_C=8.0  \text{mA},  V_{CE}=10  V, \\ &f=1.0  \text{kHz} \\ &I_E=8.0  \text{mA},  V_{CB}=10  V, \end{split}$	9.0	1.1 2.0 18 240	pF pF
NF Cob Cib Vife b'Cc	Noise Figure  Collector-Base Capacitance Input Capacitance Small-Signal Current Gain  Collector-Base Time Constant	$\begin{split} &f=60 \text{ MHz},  Rg=400  \Omega \\ &V_{CB}=10  V,  I_E=0,  f=1.0  \text{MHz} \\ &V_{EB}=0.5  V \\ &I_C=8.0  \text{mA},  V_{CE}=10  V, \\ &f=100  \text{MHz} \\ &I_C=8.0  \text{mA},  V_{CE}=10  V, \\ &f=1.0  \text{kHz} \\ &I_E=8.0  \text{mA},  V_{CB}=10  V, \\ &f=79.8  \text{MHz} \end{split}$	9.0	1.1 2.0 18 240	pF pF
NF Cob Cib Ne b'Cc	Noise Figure  Collector-Base Capacitance Input Capacitance Small-Signal Current Gain  Collector-Base Time Constant	$\begin{split} &f=60 \text{ MHz},  Rg=400  \Omega \\ &V_{CB}=10  V,  I_E=0,  f=1.0  \text{MHz} \\ &V_{EB}=0.5  V \\ &I_C=8.0  \text{mA},  V_{CE}=10  V, \\ &f=100  \text{MHz} \\ &I_C=8.0  \text{mA},  V_{CE}=10  V, \\ &f=1.0  \text{kHz} \\ &I_E=8.0  \text{mA},  V_{CB}=10  V, \\ &f=79.8  \text{MHz} \end{split}$	9.0 40 3.0	1.1 2.0 18 240	pF pF

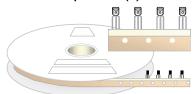
<sup>\*</sup>Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2.0%

### **TO-92 Tape and Reel Data** FAIRCHILD SEMICONDUCTOR TM **TO-92 Packaging** Configuration: Figure 1.0 **TAPE and REEL OPTION** FSCINT Label sample See Fig 2.0 for various Reeling Styles CBVK//418019 **FSCINT** Label 5 Reels per Intermediate Box Customized F63TNR Label sample Label F63TNR LOT: CBVK741B019 QTY: 2000 FSID: PN222N Customized QTY1: QTY2: 375mm x 267mm x 375mm Intermediate Box TO-92 TNR/AMMO PACKING INFROMATION **AMMO PACK OPTION** See Fig 3.0 for 2 Ammo Packing Style Quantity EOL code **Pack Options** 2,000 D26Z Е 2,000 D27Z Ammo М 2,000 D74Z 2,000 D75Z **FSCINT** Unit weight = 0.22 gm Reel weight with components = 1.04 kg Ammo weight with components = 1.02 kg Max quantity per intermediate box = 10,000 units Label 5 Ammo boxes per Intermediate Box 327mm x 158mm x 135mm Immediate Box Customized F63TNR Customized Label Label 333mm x 231mm x 183mm Intermediate Box (TO-92) BULK PACKING INFORMATION **BULK OPTION** See Bulk Packing DESCRIPTION QUANTITY Information table J18Z TO-18 OPTION STD 2.0 K / BOX Anti-static Bubble Sheets TO-5 OPTION STD NO LEAD CLIP 1.5 K / BOX J05Z **FSCINT Label** NO EOL TO-92 STANDARD STRAIGHT FOR: PKG 92, NO LEADCLIP 2.0 K / BOX 94 (NON PROELECTRON SERIES), 96 TO-92 STANDARD STRAIGHT FOR: PKG 94 (PROELECTRON SERIES BCXXX, BFXXX, BSRXXX), 97, 98 L34Z NO LEADCLIP 2.0 K / BOX 2000 units per 114mm x 102mm x 51mm EO70 box for std option Immediate Box 5 EO70 boxes per intermediate Box 530mm x 130mm x 83mm Customized Intermediate box Label FSCINT Label 10,000 units maximum per intermediate box for std option

### TO-92 Tape and Reel Data, continued

### **TO-92 Reeling Style** Configuration: Figure 2.0

### Machine Option "A" (H)



Style "A", D26Z, D70Z (s/h)

ADHESIVE TAPE IS ON BOTTOM SIDE FLAT OF TRANSISTOR IS ON BOTTOM

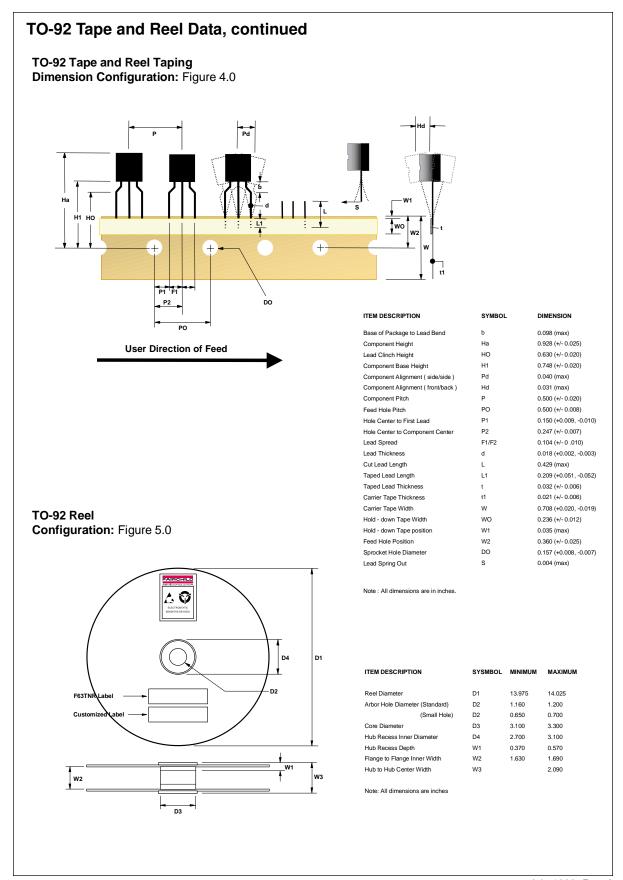
# Machine Option "E" (J)

Style "E", D27Z, D71Z (s/h)

### **TO-92 Radial Ammo Packaging** Configuration: Figure 3.0



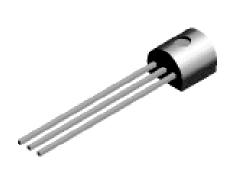


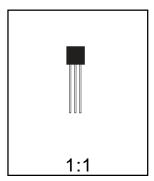


### **TO-92 Package Dimensions**



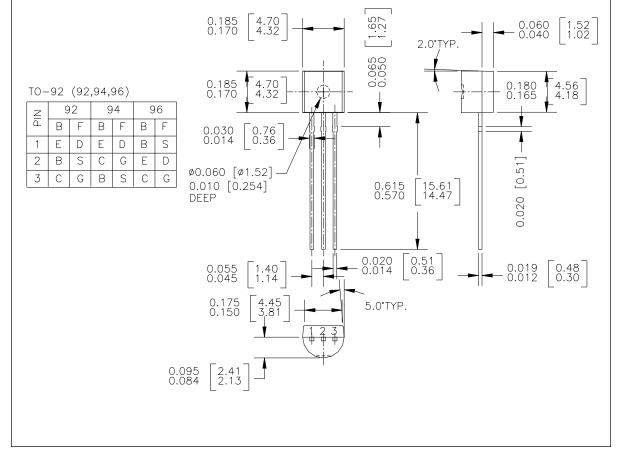
## TO-92 (FS PKG Code 92, 94, 96)





Scale 1:1 on letter size paper
Dimensions shown below are in:
inches [millimeters]

Part Weight per unit (gram): 0.1977



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Datasheet Identification	Product Status	Definition
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